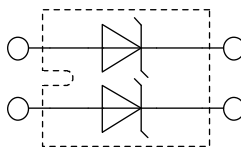


Schottky Diode

High Performance Schottky Diode
Low Loss and Soft Recovery
Parallel legs

Part number

DSS2x41-01A



Backside: isolated

E72873

Features / Advantages:

- Very low V_f
- Extremely low switching losses
- low I_{rm} values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package:

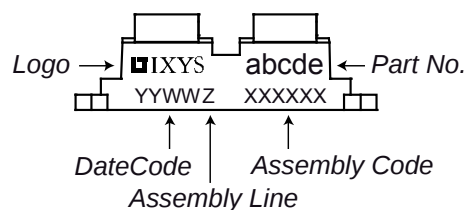
- Housing: SOT-227B (minibloc)
- Industry standard outline
- Cu base plate internal DCB isolated
- Isolation Voltage 3000 V
- Epoxy meets UL 94V-0
- RoHS compliant

Ratings

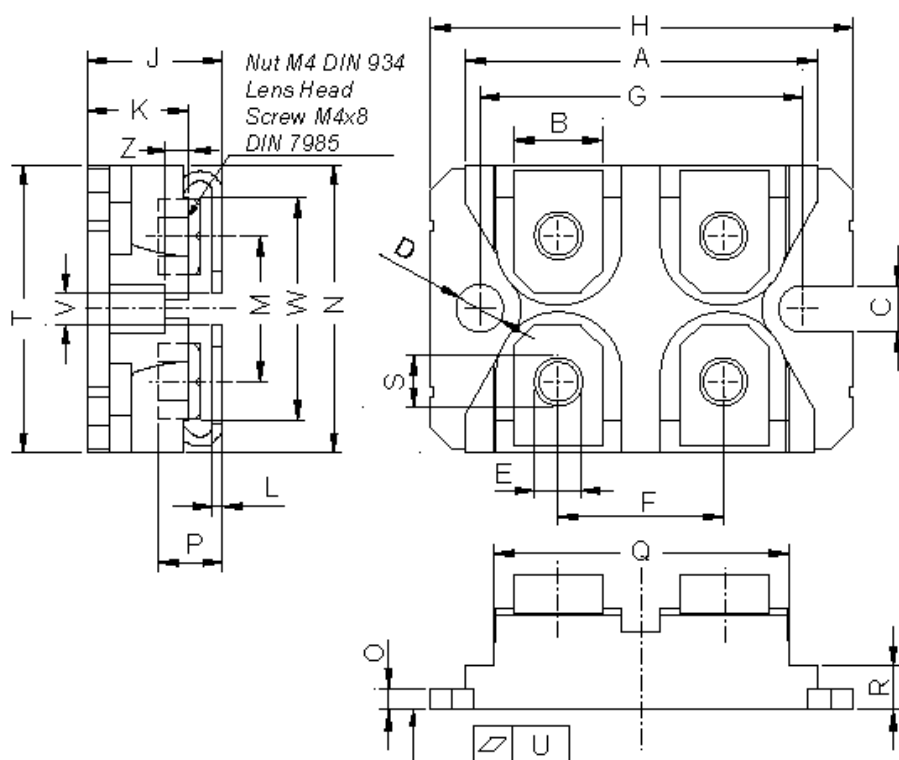
Symbol	Definition	Conditions	min.	typ.	max.	Unit
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^\circ\text{C}$			100	V
I_R	reverse current	$V_R = 100\text{ V}$ $T_{VJ} = 25^\circ\text{C}$			1	mA
		$V_R = 100\text{ V}$ $T_{VJ} = 125^\circ\text{C}$			10	mA
V_F	forward voltage	$I_F = 40\text{ A}$ $T_{VJ} = 25^\circ\text{C}$			0.88	V
		$I_F = 80\text{ A}$			1.05	V
		$I_F = 40\text{ A}$ $T_{VJ} = 125^\circ\text{C}$			0.70	V
		$I_F = 80\text{ A}$			0.88	V
I_{FAV}	average forward current	rectangular $d = 0.5$ $T_C = 110^\circ\text{C}$			40	A
V_{F0}	threshold voltage	$T_{VJ} = 150^\circ\text{C}$ for power loss calculation only			0.49	V
r_F	slope resistance				4.3	mΩ
R_{thJC}	thermal resistance junction to case				1.10	K/W
T_{VJ}	virtual junction temperature		-40		150	°C
P_{tot}	total power dissipation	$T_C = 25^\circ\text{C}$			110	W
I_{FSM}	max. forward surge current	$t = 10\text{ ms}$ (50 Hz), sine $T_{VJ} = 45^\circ\text{C}$			450	A
C_J	junction capacitance	$V_R = 12\text{ V}$; $f = 1\text{ MHz}$ $T_{VJ} = 25^\circ\text{C}$		572		pF

Symbol	Definition	Conditions	Ratings			Unit
			min.	typ.	max.	
I_{RMS}	RMS current	per terminal			70	A
R_{thCH}	thermal resistance case to heatsink			0.10		K/W
T_{stg}	storage temperature		-40		150	°C
Weight				30		g
M_D	mounting torque		1.1		1.5	Nm
M_T	terminal torque		1.1		1.5	Nm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V
$d_{Spp/App}$	creepage striking distance on surface through air	terminal to terminal	10.5	3.2		mm
$d_{Spb/Apb}$	creepage striking distance on surface through air	terminal to backside	8.6	6.8		mm

Product Marking



Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Code Key
Standard	DSS2x41-01A	DSS2x41-01A	Tube	10	475556

Outlines SOT-227B (minibloc)


Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106

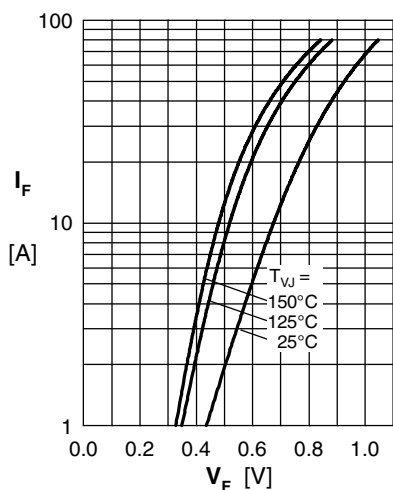


Fig. 1 Maximum forward voltage drop characteristics

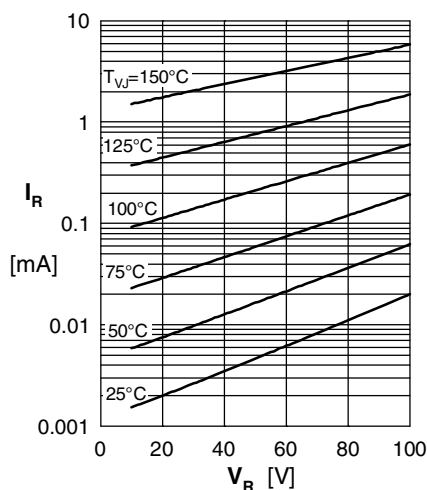


Fig. 2 Typ. reverse current I_R vs. reverse voltage V_R

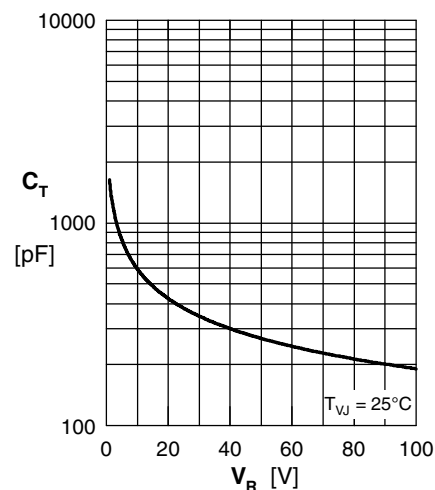


Fig. 3 Typ. junction capacitance C_T vs. reverse voltage V_R

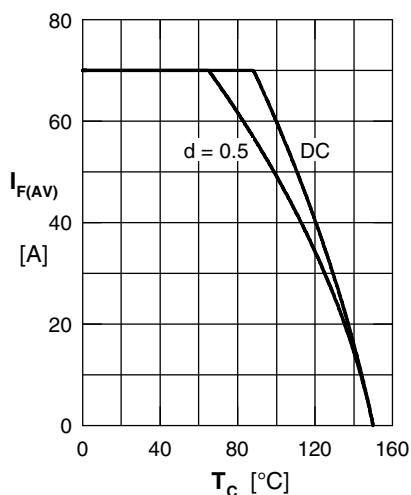


Fig. 4 Average forward current $I_{F(AV)}$ vs. case temperature T_C

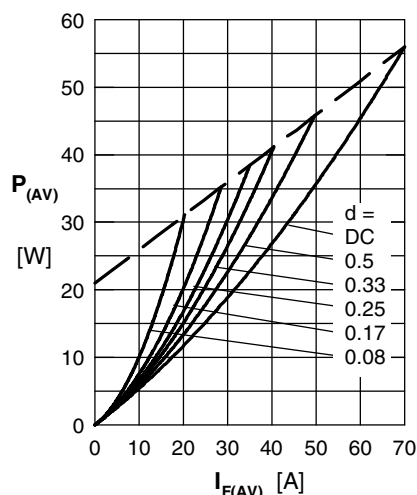


Fig. 5 Forward power loss characteristics

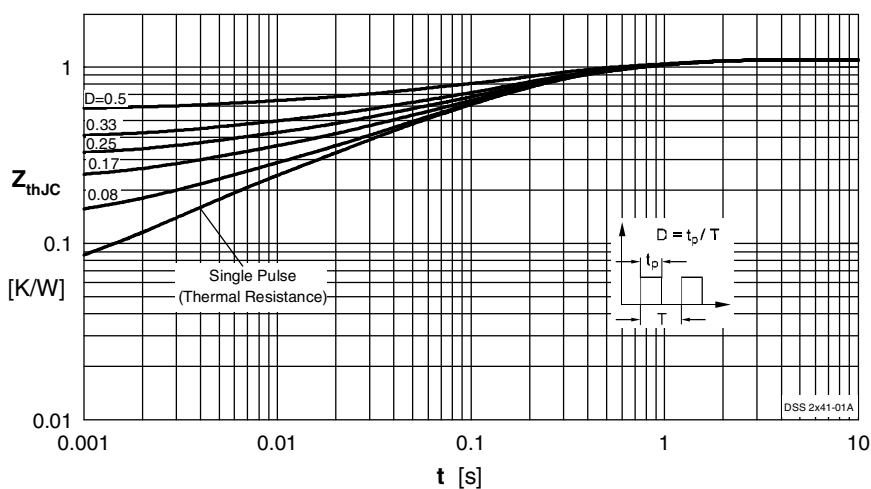


Fig. 6 Transient thermal impedance junction to case at various duty cycles

Note: All curves are per diode